

# Jiajie Lin

## List of Publications by Year in descending order

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Version: 2024-02-01

14  
papers

173  
citations

1163117

8  
h-index

1125743

13  
g-index

14  
all docs

14  
docs citations

14  
times ranked

143  
citing authors

#	ARTICLE	IF	CITATIONS
1	Wafer-Scale Fabrication of 42° Rotated Y-Cut LiTaO <sub>3</sub> -on-Insulator (LTOI) Substrate for a SAW Resonator. ACS Applied Electronic Materials, 2019, 1, 1660-1666.	4.3	40
2	Efficient ion-slicing of InP thin film for Si-based hetero-integration. Nanotechnology, 2018, 29, 504002.	2.6	26
3	Investigation on thermodynamics of ion-slicing of GaN and heterogeneously integrating high-quality GaN films on CMOS compatible Si(100) substrates. Scientific Reports, 2017, 7, 15017.	3.3	19
4	Freestanding ultrathin single-crystalline SiC substrate by MeV H ion-slicing. Applied Physics Letters, 2018, 112, .	3.3	16
5	Wafer-scale heterogeneous integration InP on trenched Si with a bubble-free interface. APL Materials, 2020, 8, .	5.1	16
6	Blister formation in He-H co-implanted InP: A comprehensive atomistic study. Applied Surface Science, 2021, 552, 149426.	6.1	14
7	Realization of wafer-scale single-crystalline GaN film on CMOS-compatible Si(100) substrate by ion-cutting technique. Semiconductor Science and Technology, 2020, 35, 125004.	2.0	13
8	Thermodynamics of Ion-Cutting of $\text{In}^2\text{-Ga}_{2\text{O}_3}$ and Wafer-Scale Heterogeneous Integration of a $\text{In}^2\text{-Ga}_{2\text{O}_3}$ Thin Film onto a Highly Thermal Conductive SiC Substrate. ACS Applied Electronic Materials, 2022, 4, 494-502.	4.3	12
9	InAs/GaAs quantum dot laser epitaxially grown on on-axis (001) GaAsOI substrate. Optics Express, 2021, 29, 38465-38476.	3.4	4
10	Stress and strain analysis of Si-based III-V template fabricated by ion-slicing*. Chinese Physics B, 2020, 29, 077303.	1.4	3
11	Si-based InGaAs photodetectors on heterogeneous integrated substrate. Science China: Physics, Mechanics and Astronomy, 2021, 64, 1.	5.1	3
12	High yield preparation of flexible single-crystalline 4H-silicon carbide nanomembranes via buried micro-trenches. Optical Materials, 2021, 115, 111068.	3.6	3
13	InAs triangular quantum wells grown on InP/SiO <sub>2</sub> /Si heterogeneous substrate for mid-infrared emission. Materials Science in Semiconductor Processing, 2021, 136, 106163.	4.0	2
14	Efficient heterogeneous integration of InP/Si and GaSb/Si templates with ultra-smooth surfaces. Science China Information Sciences, 2022, 65, .	4.3	2